

**Form PTO-1449** (modified)List of Patents and Publications  
For Applicant's Information

Disclosure Statement

(Use several sheets if necessary)

ATTY. DOCKET NO.  
MCRO:017-7/FLESERIAL NO.  
UnassignedAPPLICANT  
Fernando Gonzalez et al.FILING DATE  
HerewithGROUP  
Unassigned**U.S. PATENT DOCUMENTS**

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
TL	A1	3,241,009	03/15/66	Dewald et al.	317	234	11/06/61
	A2	3,423,646	01/21/69	Cubert et al.	317	234	02/01/65
	A3	3,602,635	08/31/71	Romankiw	174	68.5	06/30/70
	A4	3,699,543	10/17/72	Neale	340	173R	12/22/69
	A5	3,796,926	03/12/74	Colé et al.	317	234 R	03/29/71
	A6	3,877,049	04/08/75	Buckley	357	2	11/28/73
	A7	3,886,577	05/27/75	Buckley	357	2	09/12/73
	A8	4,099,260	07/04/78	Lynes et al.	365	105	09/20/76
	A9	4,115,872	09/19/78	Bluhm	365	163	05/31/77
	A10	4,174,521	11/13/79	Neale	357	45	04/06/78
	A11	4,194,283	03/25/80	Hoffmann	29	571	08/16/78
	A12	4,227,297	10/14/80	Angerstein	29	571	07/31/78
	A13	4,203,123	05/13/80	Shanks	357	2	12/12/77
	A14	4,272,562	06/09/81	Wood	427	87	06/19/79
	A15	4,420,766	12/13/83	Kasten	357	59	02/09/81
	A16	4,433,342	02/21/84	Patel et al.	357	2	04/06/81
	A17	4,458,260	07/03/84	McIntyre et al.	357	30	11/20/81
	A18	4,499,557	02/12/85	Holmberg et al.	365	163	07/06/81
	A19	4,502,208	03/05/85	McPherson	29	584	08/26/83
	A20	4,502,914	03/05/85	Trumpf et al.	156	643	10/28/83
	A21	4,569,698	02/11/86	Feist	148	1.5	05/31/85
	A22	4,630,355	12/23/86	Johnson	29	575	03/08/85
	A23	4,641,420	02/10/87	Lee	29	511	08/30/84
✓	A24	4,642,140	02/10/87	Noufi et al.	148	6.24	04/30/85
TL	A25	4,666,252	05/19/87	Yaniv et al.	350	333	06/29/84

TL	A26	4,677,742	07/07/87	Johnson	29	591	12/05/83
	A27	4,757,359	07/12/88	Chiao et al.	357	23.5	04/07/86
	A28	4,795,657	01/03/89	Formigoni et al.	427	96	04/08/85
	A29	4,804,490	02/14/89	Pryor et al.	252	62.3 BT	10/13/87
	A30	4,809,044	02/28/89	Pryor et al.	357	2	11/26/86
	A31	4,823,181	04/18/89	Mohsen et al.	357	51	05/09/86
	A32	4,876,220	10/24/89	Mohsen et al.	437	170	11/13/87
	A33	4,876,668	10/24/89	Thakoor et al.	365	163	04/29/86
	A34	4,881,114	11/14/89	Mohsen et al.	357	54	05/16/86
	A35	4,892,840	01/09/90	Esquivel et al.	437	52	04/11/89
	A36	5,144,404	09/01/92	Iranmanesh et al.	357	51	08/22/90
	A37	5,166,096	11/24/92	Cote et al.	437	195	04/14/92
	A38	5,166,758	11/24/92	Ovshinsky et al.	257	3	01/18/91
	A39	5,177,567	01/05/93	Klersy et al.	257	4	07/19/91
	A40	5,216,282	06/01/93	Cote et al.	257	773	10/29/91
	A41	5,233,217	08/03/93	Dixit et al.	257	530	05/03/91
	A42	5,293,335	03/08/94	Pernisz et al.	365	148	12/09/92
	A43	5,296,716	03/22/94	Ovshinsky et al.	257	3	08/19/91
	A44	5,310,693	05/10/94	Hsue	437	43	06/24/93
	A45	5,335,219	08/02/94	Ovshinsky et al.	369	288	09/30/91
	A46	5,341,328	08/23/94	Ovshinsky et al.	365	163	06/15/92
	A47	5,359,205	10/25/94	Ovshinsky	257	3	05/08/92
	A48	5,363,329	11/08/94	Troyan	365	184	11/10/93
	A49	5,406,125	04/11/95	Johnson et al.	257	774	04/15/93
	A50	5,414,271	05/09/95	Ovshinsky et al.	257	3	11/07/91
	A51	5,429,988	07/04/95	Huang et al.	437	187	06/13/94
	A52	5,510,629	04/23/96	Karpovich et al.	257	50	05/27/94
	A53	5,534,711	07/09/96	Ovshinsky et al.	257	3	04/19/95
	A54	5,534,712	07/09/96	Ovshinsky et al.	217	3	08/21/95
	A55	5,536,947	07/16/96	Klersy et al.	257	3	07/25/95
	A56	5,569,932	10/29/96	Shor et al.	257	3	01/23/95
	A57	5,578,185	11/26/96	Bergeron et al.	205	123	01/31/95
	A58	5,675,187	10/07/97	Numata et al.	257	758	05/16/96

## FOREIGN PATENT DOCUMENTS

EXAM. INT.	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
TL	B1	1 319 388	06/06/73	Great Britain	H01L	9/00	Yes
TL	B2	0 117 045	08/29/84	EPA	H01L	45/00	Yes
TL	B3	JP 60109266	06/14/85	Japan	H01L	27/10	Yes

## OTHER ART (Author, Title, Journal, Volume, Pertinent Pages, & Date)

TL	C1	Kim and Kim, "Effects of High-Current Pulses on Polycrystalline Silicon Diode with n-type Region Heavily Doped with Both Boron and Phosphorus," <i>J. Appl. Phys.</i> , 53(7):5359-5360, 1982.
	C2	Neale and Aseltine, "The Application of Amorphous Materials to Computer Memories," <i>IEEE</i> , 20(2):195-205, 1973.
	C3	Pein and Plummer, "Performance of the 3-D Sidewall Flash EPROM Cell," <i>IEEE</i> , 11-14, 1993.
	C4	Post and Ashburn, "Investigation of Boron Diffusion in Polysilicon and its Application to the Design of p-n-p Polysilicon Emitter Bipolar Transistors with Shallow Emitter Junctions," <i>IEEE</i> , 38(11):2442-2451, 1991.
	C5	Post <i>et al.</i> , "Polysilicon Emitters for Bipolar Transistors: A Review and Re-Evaluation of Theory and Experiment," <i>IEEE</i> , 39(7):1717-1731, 1992.
	C6	Post and Ashburn, "The Use of an Interface Anneal to Control the Base Current and Emitter Resistance of p-n-p Polysilicon Emitter Bipolar Transistors," <i>IEEE</i> , 13(8):408-410, 1992.
	C7	Rose <i>et al.</i> , "Amorphous Silicon Analogue Memory Devices," <i>J. Non-Crystalline Solids</i> , 115:168-170, 1989.
	C8	Schaber <i>et al.</i> , "Laser Annealing Study of the Grain Size Effect in Polycrystalline Silicon Schottky Diodes," <i>J. Appl. Phys.</i> , 53(12):8827-8834, 1982.
	C9	Yamamoto <i>et al.</i> , "The I-V Characteristics of Polycrystalline Silicon Diodes and the Energy Distribution of Traps in Grain Boundaries," <i>Electronics and Communications in Japan</i> , Part 2, 75(7):51-58, 1992.
	C10	Yeh <i>et al.</i> , "Investigation of Thermal Coefficient for Polycrystalline Silicon Thermal Sensor Diode," <i>Jpn. J. Appl. Phys.</i> , 31(Part 1, No. 2A):151-155, 1992.
	C11	Oakley <i>et al.</i> , "Pillars - The Way to Two Micron Pitch Multilevel Metallisation," <i>IEEE</i> , 23-29, 1984.
↓	C12	Prince, "Semiconductor Memories," A Handbook of Design, Manufacture, and Application, 2 <sup>nd</sup> Ed., pgs. 118-123.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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